

*ABSTRACT AMENDMENTS*

Replace the Abstract with:

A method for manufacturing a semiconductor device includes ~~the steps of~~ forming a first insulating film on a substrate, forming a second insulating film on the first insulating film, and forming a gate electrode on the second insulating film. ~~The step of forming a~~ Forming the second insulating film has a first step of ~~includes~~ supplying film-forming materials and ~~making adsorbing~~ the film-forming materials ~~adsorbed~~ on the first insulating film, ~~a second step of~~ purging the film-forming materials that ~~has have~~ not been adsorbed, ~~a third step of~~ supplying oxidants to oxidize the adsorbed film-forming materials, and ~~a fourth step of~~ purging the oxidants that ~~has have~~ not contributed to oxidization. ~~The step of forming a~~ Forming the second insulating film is repeated for a plurality of ~~in~~ cycles, continuously, and the purging time ~~in the fourth step of the oxidants~~ in the ~~an~~ initial predetermined number of the cycles is made longer than the purging time ~~in the fourth step of the oxidants~~ in ~~following~~ cycles following the initial number of cycles.